WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:
an insulating layer;
an interconnect line embedded in said insulating layer;
a circuit element mounted on said insulating layer;
a packaging layer formed to cover said circuit element; and
an electroconductive shielding film formed to cover said packaging layer,
wherein said interconnect line is electrically coupled to said shielding film.

2. The semiconductor device according to claim 1, further comprising a protective film formed to cover said shielding film, said protective film comprising a material having higher corrosion resistance than that of a material that is included in said shielding film.

3. A method for manufacturing a semiconductor device having a circuit element by dividing a multi-layer member, said multi-layer member comprising an insulating layer; an interconnect line embedded in said insulating layer; said circuit element mounted on a surface of said insulating layer; and a packaging layer formed to cover said circuit element, comprising:
forming a dividing gutter on a surface of said multi-layer member to create an exposed side surface of said interconnect line;
covering the front surface of said multi-layer member with an electroconductive material to form a shielding film, said shielding film being electrically coupled to said interconnect line; and

cutting said multi-layer member off from the backside thereof along said dividing gutter to separate said circuit element of the multi-layer member from the rest regions thereof.

4. The method according to claim 3, further comprising: grounding said interconnect line.

5. The method according to claim 3 , further comprising:
wherein a plurality of the circuit elements are mounted on said insulating layer, and said interconnect line is provided to be coupled to said plurality of the circuit elements before forming said dividing gutter, and
wherein said dividing gutter includes dividing said interconnect line so that each of the divided interconnect lines is coupled to each of said circuit elements, respectively.

6. The method according to claim 4, further comprising:
wherein a plurality of the circuit elements are mounted on said insulating layer, and said interconnect line is provided to be coupled to said plurality of the circuit elements before forming said dividing gutter, and
wherein said dividing gutter includes dividing said interconnect line so that each of the divided interconnect lines is coupled to each of said circuit elements, respectively.

7. The method according to claim 3, further comprising:
covering said shielding film with a protective film, said protective film comprising a material having higher corrosion resistance than that of a material which is included in said shielding film.

8. The method according to claim 4, further comprising:
covering said shielding film with a protective film, said

protective film comprising a material having higher corrosion resistance than that of a material which is included in said shielding film.

5 9. The method according to claim 5, further comprising:

covering said shielding film with a protective film, said protective film comprising a material having higher corrosion resistance than that of a material which is included in said shielding film.

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